



Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
	90mΩ @ V _{GS} = -10V	-3.8A
-30V	134mΩ @ V _{GS} = -4.5V	-3.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDs(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Load Switch for Portable Devices

P-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMG2307LQ)

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
 - Weight: 0.08 grams (Approximate)

Gate Gate Source Government Gover

Ordering Information (Note 4)

Part Number	Package	Packing			
Fait Nulliper	Fackage	Qty.	Carrier		
DMG2307L-7	SOT23	3,000	Tape & Reel		

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https:///www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Date Code Key			G	 24 ;	M A	YI Y	24 = Produ M = Date C or Ÿ = Yea = Month (r	Code Marki ar (ex: J = 2	2022)	le		
Year	2011		2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Y		J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage			Vgss	±20	V
Continuous Drain Current (Note 5) $V_{GS} = -10V$	Steady State	TA = +25°C TA = +70°C	ID	-2.5 -2.0	А
Continuous Drain Current (Note 6) $V_{GS} = -10V$	Steady State	TA = +25°C TA = +70°C	ID	-3.8 -3.0	А
Continuous Drain Current (Note 6) V _{GS} = -10V	t ≦10sec	TA = +25°C TA = +70°C	ID	-4.6 -3.6	A
Continuous Drain Current (Note 6) V _{GS} = -4.5V Steady State		TA = +25°C TA = +70°C	ID	-3.1 -2.5	A
Pulsed Drain Current (Note 6)			Ідм	-20	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

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Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	0.76	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	159	°C/W
Total Power Dissipation (Note 6)	PD	1.36	W
Thermal Resistance, Junction to Ambient (Note 6)	Reja	94	°C/W
Total Power Dissipation (Note 6) $t \leq 10 \text{sec}$	PD	1.9	W
Thermal Resistance, Junction to Ambient (Note 6) t \leq 10sec	Reja	65.8	°C/W
Operating and Storage Temperature Range	Tj, Tstg	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BVDSS	-30	_		V	$V_{GS} = 0V, I_{D} = -250 \mu A$
Zero Gate Voltage Drain Current @Tc = +25°C	ldss	_	_	-1.0	μA	$V_{DS} = -30V$, $V_{GS} = 0V$
Gate-Source Leakage	Igss			±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	VGS(TH)	-1.0		-3.0	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$
Static Drain-Source On-Resistance	Basian		70	90	mΩ	$V_{GS} = -10V, I_{D} = -2.5A$
Static Drain-Source On-Resistance	RDS(ON)		105	134	11122	$V_{GS} = -4.5V, I_D = -2.5A$
Forward Transfer Admittance	Yfs		4.8		s	V _{DS} = -10V, I _D = -2.5A
Diode Forward Voltage (Note 6)	Vsd		-0.75	-1.0	V	$V_{GS} = 0V$, $I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss		371.3	_	pF	
Output Capacitance	Coss		51.3		pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss		45.9		pF	1 - 1.00012
Gate Resistance	Rg		17		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg		4.0		nC	
Total Gate Charge (V _{GS} = -10V)	Qg		8.2		nC	$V_{GS} = -10V, V_{DS} = -15V,$
Gate-Source Charge	Qgs		0.9		nC	I _D = -3A
Gate-Drain Charge	Qgd		1.2		nC	
Turn-On Delay Time	td(on)		4.8		ns	
Turn-On Rise Time	t _R		7.3		ns	V _{DS} = -15V, V _{GS} = -10V, R _L = 15Ω, R _G = 6Ω,
Turn-Off Delay Time	tD(OFF)		22.4		ns	$R_L = 15\Omega, R_G = 6\Omega,$ $I_D = -1A$
Turn-Off Fall Time	tF		13.4		ns	

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

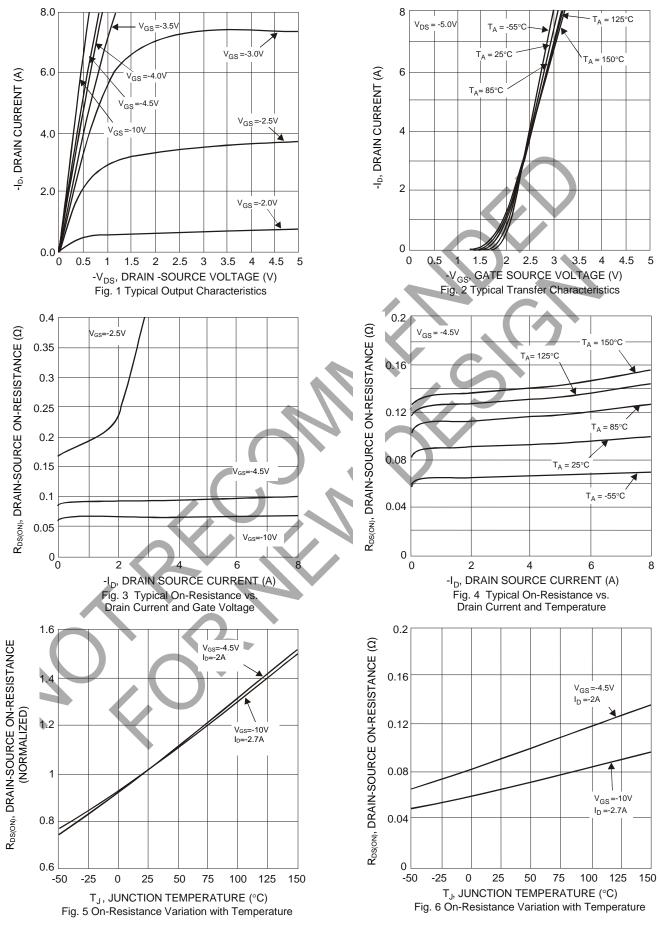
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.

7. Short duration pulse test used to minimize self-heating effect.

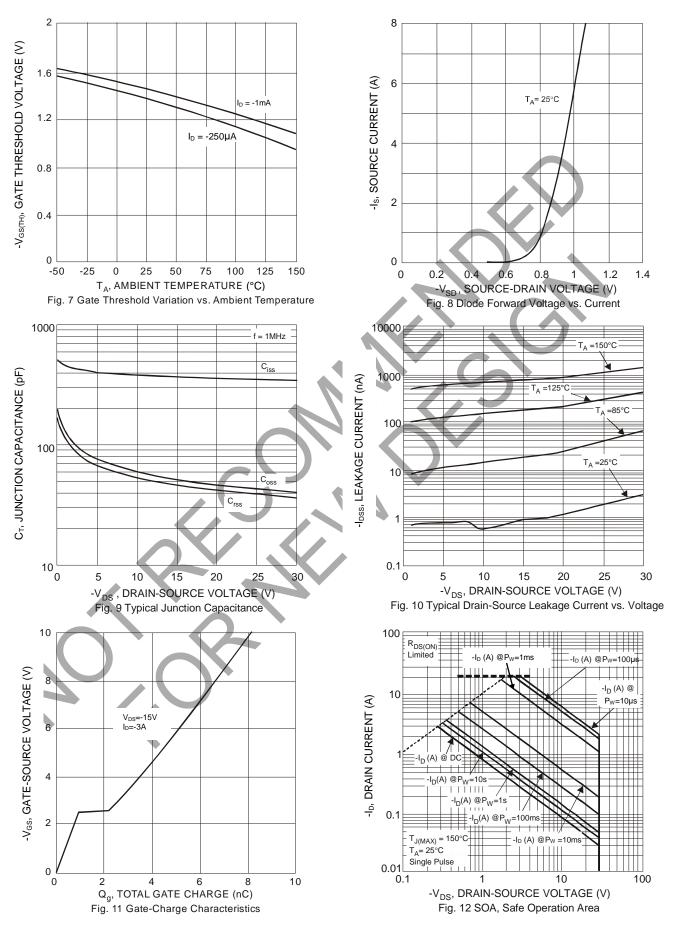
8. Guaranteed by design. Not subject to product testing.



DMG2307L

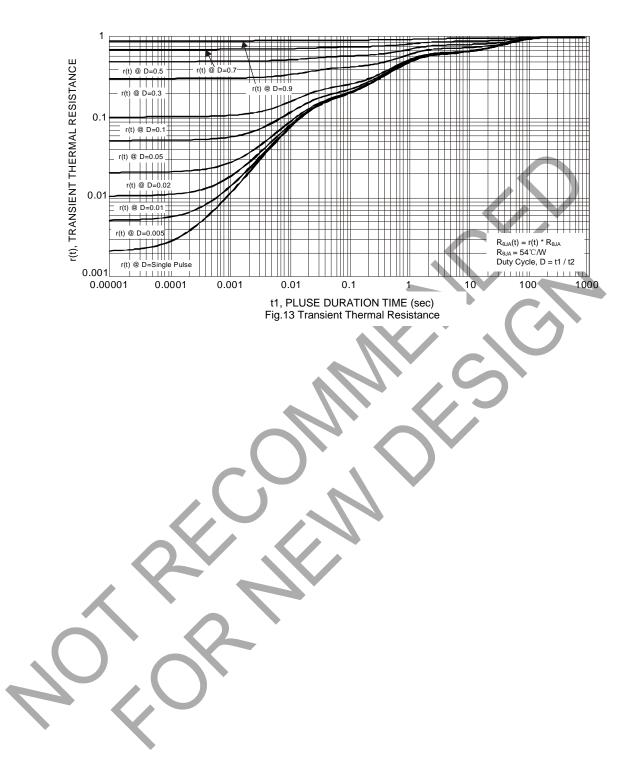






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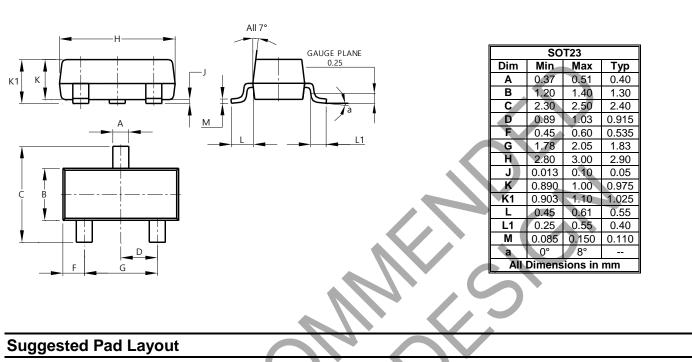






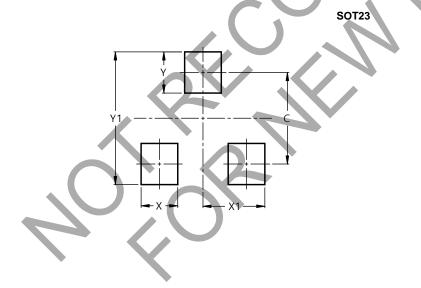
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23

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Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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